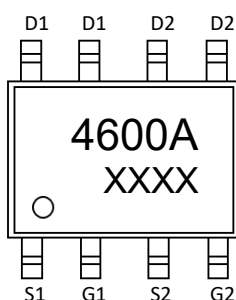


Features

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery protection
- Load switch
- Power management

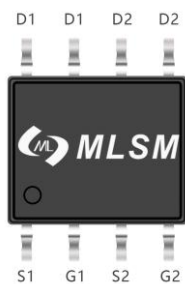


4600A : Device code
XXXX : Code

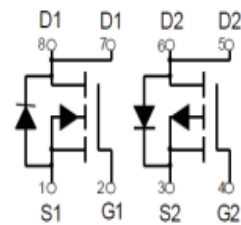
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
30V	22.6mΩ@10V	6.9A
	27mΩ@4.5V	
-30V	42.5mΩ@-10V	-5.0A
	54mΩ@-4.5V	



SOP-8 top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	N-Channel	P-Channel	Unit
V_{DS}	Drain-Source Breakdown Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	±12	±12	V
T_J	Maximum Junction Temperature	150	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
I_S	Diode Continuous Forward Current	Tc=25°C		A
		6.9	-5	

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	Tc=25°C	40	-30	A
I_D	Continuous Drain Current	Tc=25°C	6.9	-5	A
P_D	Maximum Power Dissipation	Tc=25°C	2	2	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		62.5	50	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MQ4600A	SOP-8	4600A	3,000	6,000	42,000	13"reel



N-Ch Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.7	0.9	1.4	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =6.9A	--	22.6	27	mΩ
		V _{GS} =4.5V, I _D =6.0A	--	27	32	mΩ
		V _{GS} =2.5V, I _D =5.0A	--	42	50	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	632	--	pF
C _{OSS}	Output Capacitance		--	58	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	70	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =15V, I _D =6.9A, V _{GS} =10V	--	17	--	nC
Q _{gs}	Gate Source Charge		--	2	--	nC
Q _{gd}	Gate Drain Charge		--	2	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, R _L =4.1Ω, V _{GS} =10V, R _G =3Ω	--	4.5	--	nS
t _r	Turn-on Rise Time		--	28.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	16.5	--	nS
t _f	Turn-Off Fall Time		--	26	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=6.9A	--	--	1.2	V

P-Ch Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.7	--	-1.4	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-5A	--	42.5	49	mΩ
		V _{GS} =-4.5V, I _D =-4A	--	54	64	mΩ
		V _{GS} =-2.5V, I _D =-1A	--	80	120	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	770	--	pF
C _{OSS}	Output Capacitance		--	440	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	123	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-5A, V _{GS} =-15V	--	30	--	nC
Q _{gs}	Gate Source Charge		--	2.7	--	nC
Q _{gd}	Gate Drain Charge		--	6.9	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-15V, I _D =-5A, V _{GS} =-10V, R _G =2.5Ω	--	9	--	nS
t _r	Turn-on Rise Time		--	16	--	nS
t _{d(off)}	Turn-Off Delay Time		--	77	--	nS
t _f	Turn-Off Fall Time		--	40	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=-5A	--	--	-1.2	V

N-Channel Typical Operating Characteristics

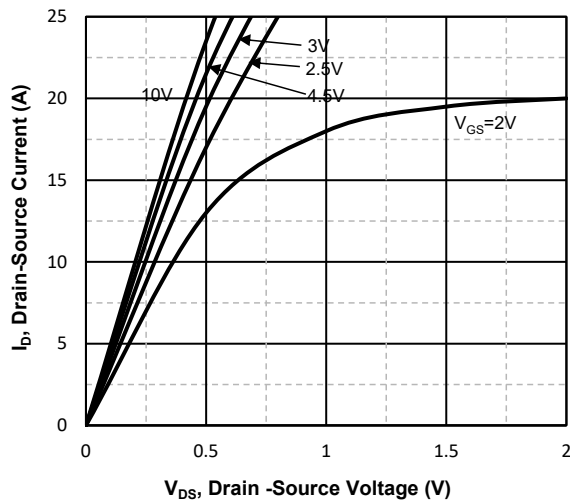


Fig1. Typical Output Characteristics

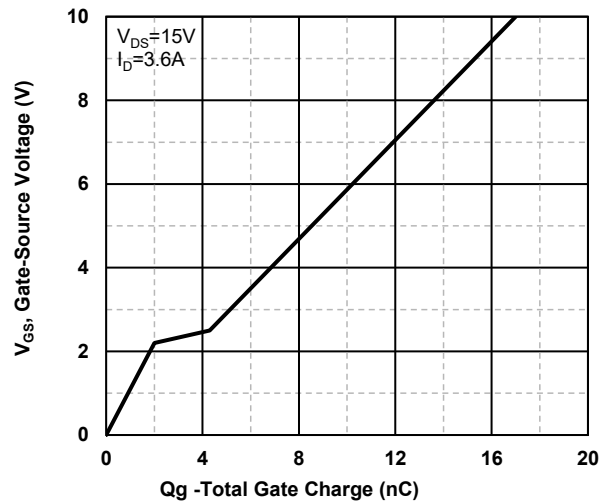


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

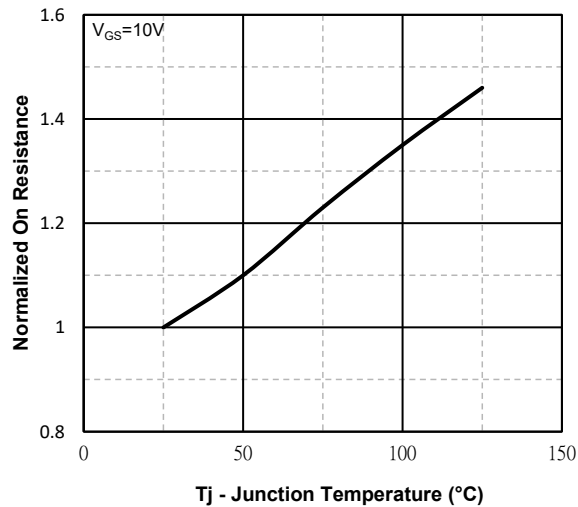


Fig3. Normalized On-Resistance Vs. Temperature

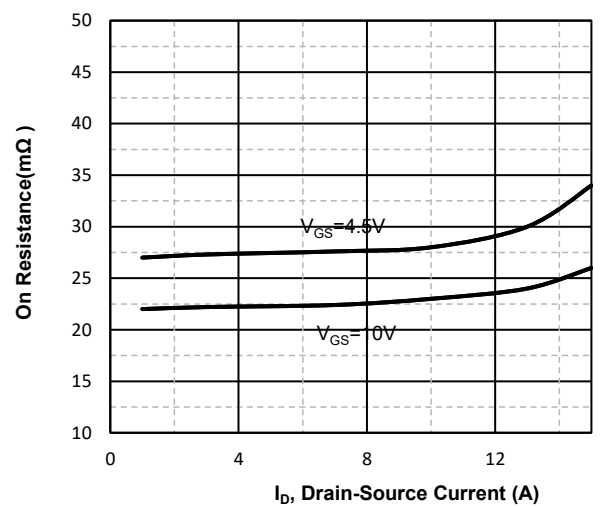


Fig4. On-Resistance Vs. Drain-Source Current

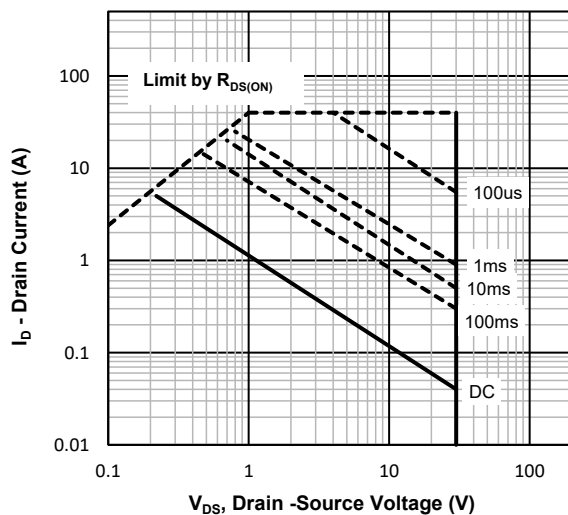


Fig5. Maximum Safe Operating Area

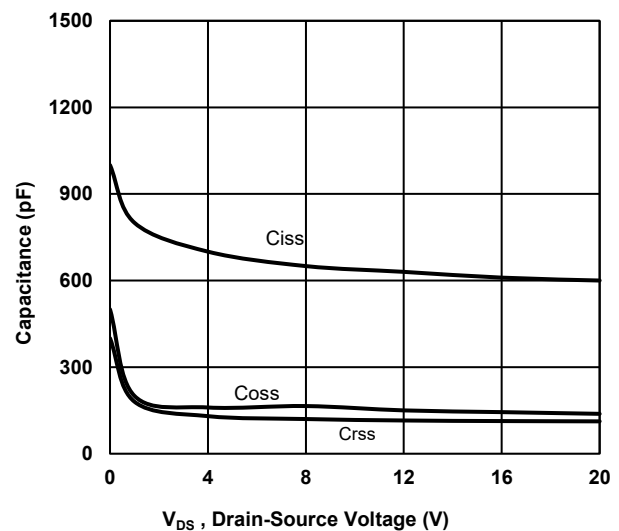


Fig6. Typical Capacitance Vs. Drain-Source Voltage

P-Channel Typical Operating Characteristics

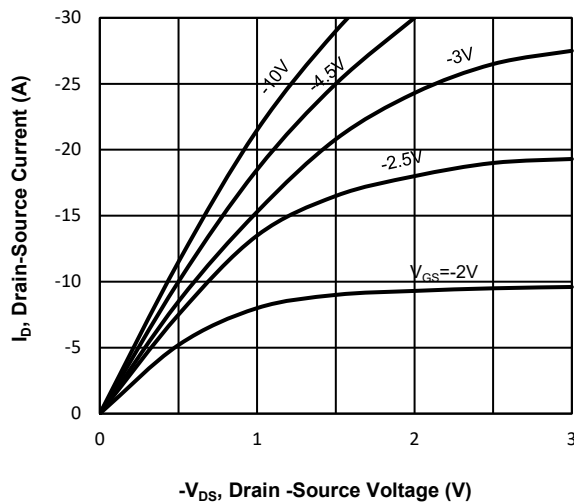


Fig7. Typical Output Characteristics

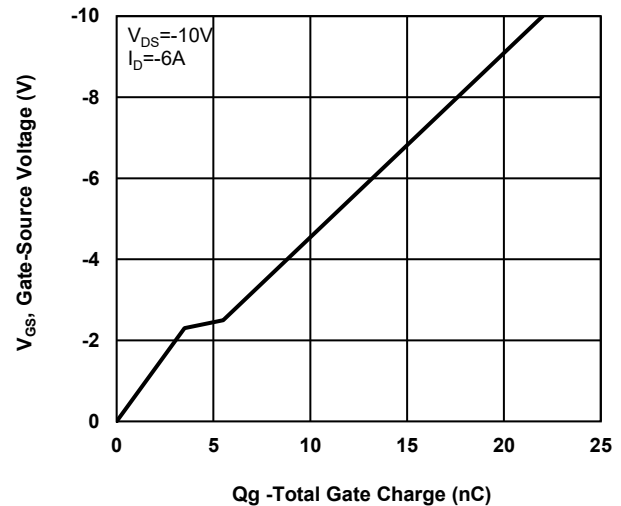


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

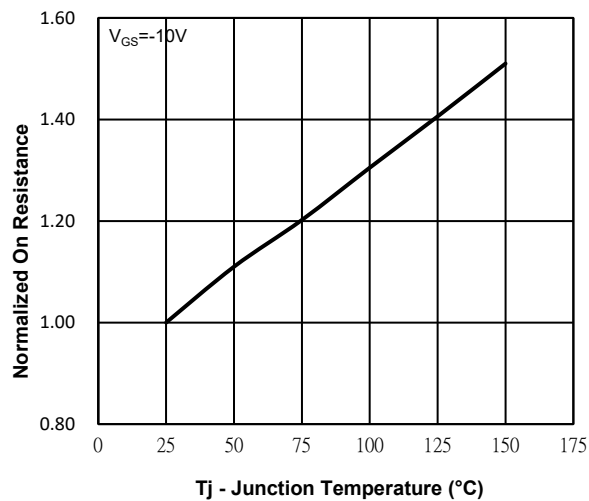


Fig9. Normalized On-Resistance Vs. Temperature

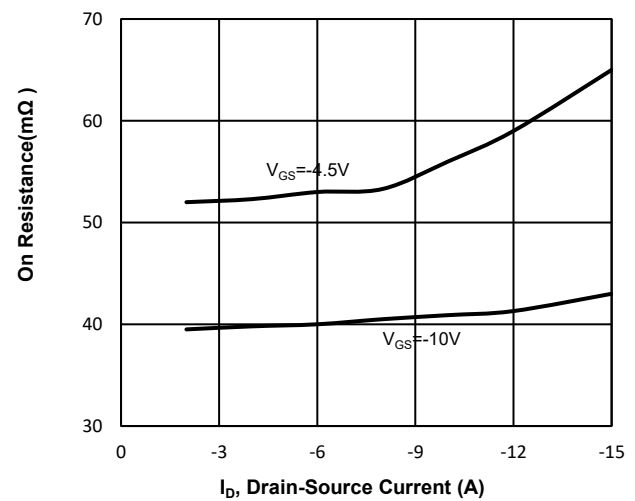


Fig10. On-Resistance Vs. Drain-Source Current

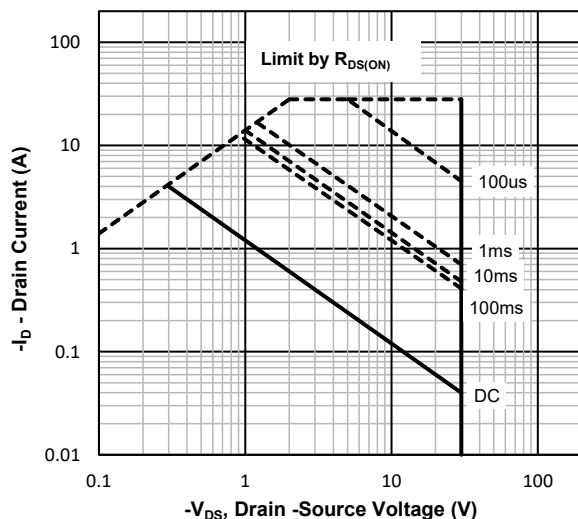


Fig11. Maximum Safe Operating Area

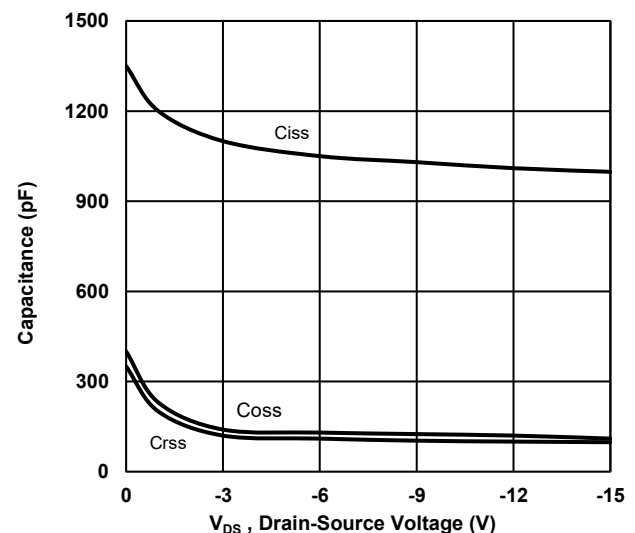
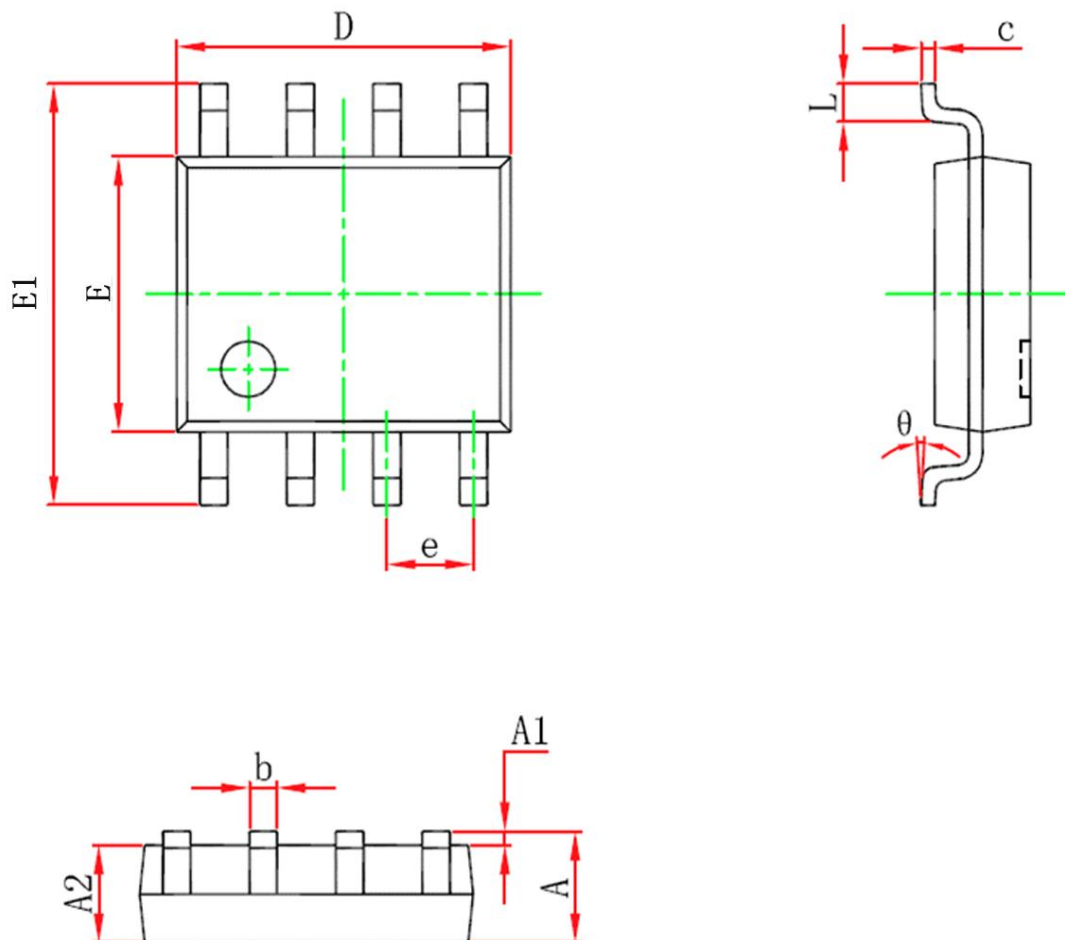


Fig12. Typical Capacitance Vs. Drain-Source Voltage

SOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°